

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Emmanuel Hadji et al.

Title: METHOD FOR FORMING AN OPTICAL SILICON LAYER ON A SUPPORT
AND USE OF SAID METHOD IN THE PRODUCTION OF OPTICAL
COMPONENTS

Docket No.: 33019US1

INFORMATION DISCLOSURE STATEMENT

Mail Stop PATENT APPLICATION
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with 37 C.F.R. § 1.98, applicant is submitting herewith Form PTO-1449 listing references for consideration by the Examiner. Per 37 C.F.R. § 1.98(d), copies of the references are not required since each reference listed was cited in application Serial No. 09/673,005 filed November 27, 2000.

Respectfully submitted,

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Date: March 15, 2004

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Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 33019US1	SERIAL NO. TBD
INFORMATION DISCLOSURE CITATION BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY) Page 1 of 1		APPLICANT: Emmanuel Hadji et al.	
		FILING DATE: Herewith	GROUP ART UNIT: TBD

U.S. PATENT DOCUMENTS							
Exam. Itl.		Document No.	Date	Name	Class	Subclass	Filing Date
	A	4,848,272	7/1989	Ohmura et al.	118	50.1	
	B	5,013,681	5/1991	Godbey et al.	438	459	
	C	5,363,398	11/1994	Glass et al.			
	D	5,374,564	12/1994	Bruel			
	E	5,835,521	11/1998	Ramdani et al.	372	50	
	F	5,838,065	11/1998	Hamburgen et al.	257	722	
	G	5,993,677	11/1999	Biasse et al.	216	36	
	H	5,985,687	11/1999	Bowers et al.	438	29	
	I	6,008,110	12/1999	Samata et al.	438	459	
	J	6,013,912	1/2000	Pautrat et al.	250	214.1	
	K	6,046,065	4/2000	Goldstein et al.	372	43	

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		Document No.	Date	Country	Class	Subclass	Translation
	L	0 578 407	1/1994	EP			

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)		
M	Yukari Ishikawa et al., Epitaxy-ready Si/SiO ₂ Bragg reflectors by multiple separation-by-implanted-oxygen, Dec. 16, 1996, pages 3881-3883.	
N	E.F. Schubert et al., Giant enhancement of luminescence intensity in Er-doped Si/SiO ₂ resonant cavities, Sept. 21, 1992, pages 1381-1383.	
P	R.A. Soref et al., Silicon intersubband lasers, 1998, pages 427-439.	
Q	Richard A. Soref, Prospects for novel si-based optoelectronic devices: unipolar and p-i-p-i lasers, July, 1992, pages 325-329.	
R	Michio Tajima et al., Luminescence due to electron-hole condensation in silicon-on-insulator, August, 1998, pages 2224-2228.	
S	M. Tajima et al., Characterization of bond and etch-back silicon-on-insulator wafers by photoluminescence under ultraviolet excitation, January, 1997, pages 231-233.	

Examiner:	Date Considered
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*Examiner: Initial if reference considered, regardless of whether citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.